

Vishay Siliconix

Dual N-Channel 30 V (D-S) MOSFET

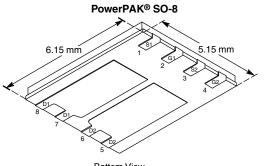
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
30	0.022 at V _{GS} = 10 V	10		
	0.030 at V _{GS} = 4.5 V	8.5		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

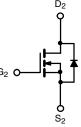


HALOGEN FREE Available



Bottom View

Ordering Information: Si7844DP-T1-E3 (Lead (Pb)-free) Si7844DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T	A = 25 °C, unle	ess otherwise	noted)		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _A = 25 °C	– I _D	10	6.4	А
Continuous Drain Current $(T_j = 150^{\circ} C)$	T _A = 70 °C		8.0	5.1	
Pulsed Drain Current		I _{DM}	20		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	2.9	1.1	
Maximum Power Dissipation ^a	T _A = 25 °C	– P _D	3.5	1.4	W
Maximum Fower Dissipation	T _A = 70 °C		2.2	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	. R _{thJA} R _{thJC}	26	35		
Maximum Junction-to-Ambient ^a	Steady State		60	85	°C/W	
Maximum Junction-to-Case (Drain)	Steady State		3.9	5.5		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.8		2.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1		
	IDSS	V_{DS} = 30 V, V_{GS} = 0 V, T_{J} = 55 °C			5	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, V_{GS} = 10 V	20			Α	
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$		0.018	0.022	Ω	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 8.5 \text{ A}$		0.024	0.030		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		22		S	
Diode Forward Voltage ^a	V _{SD}	$I_{S} = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			13	20	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		2			
Gate-Drain Charge	Q _{gd}			2.7			
Gate Resistance	Rg		0.5		3.2	Ω	
Turn-On Delay Time	t _{d(on)}			8	16		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	20	7	
Turn-Off Delay Time	t _{d(off)}	$t_{d(off)}$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 6 \Omega$		21	40	ns	
Fall Time	t _f			10	20]	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs		40	80		

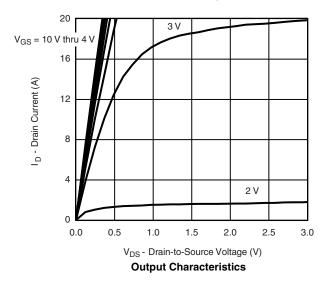
Notes:

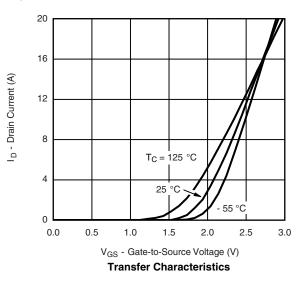
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



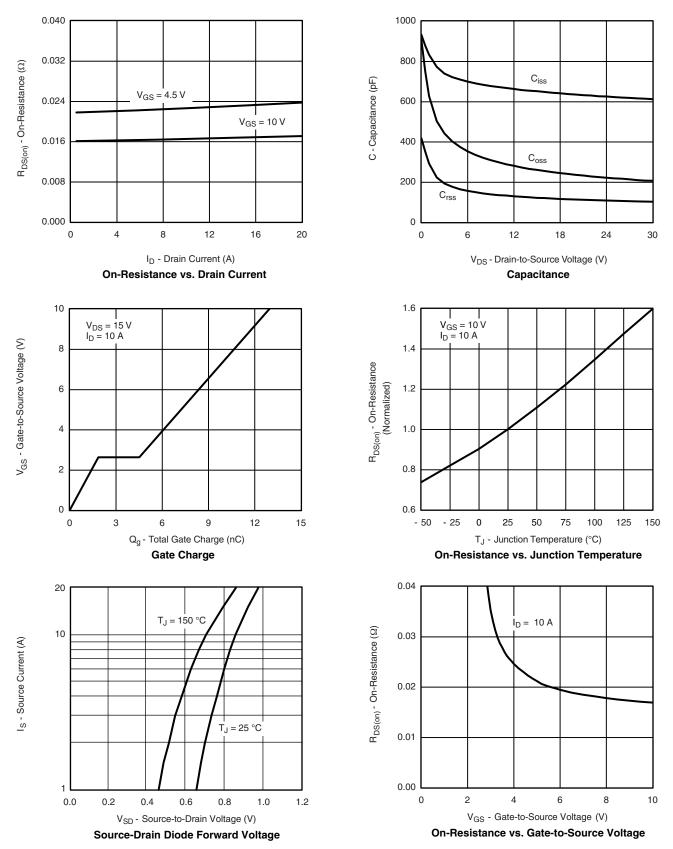




Si7844DP

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

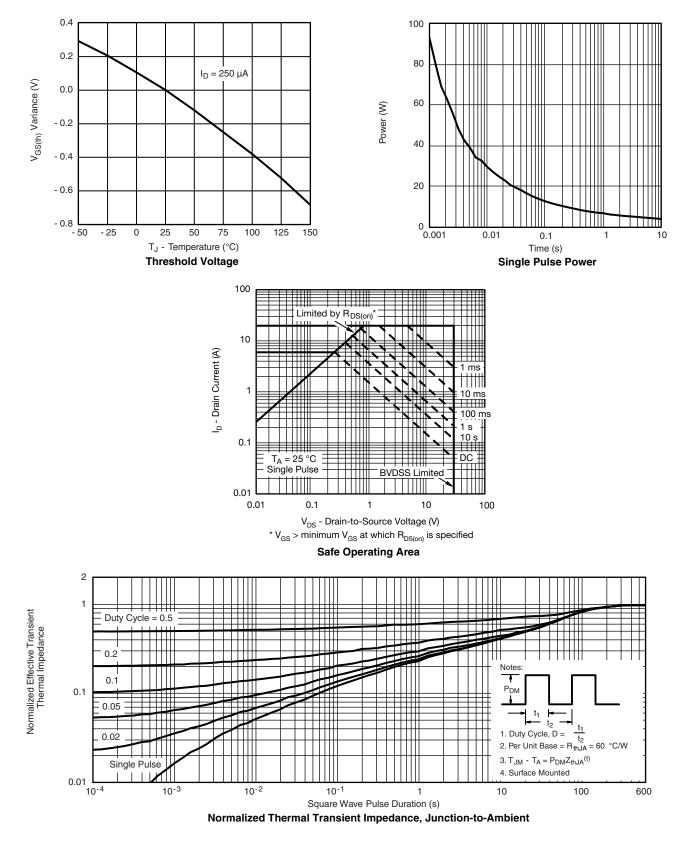


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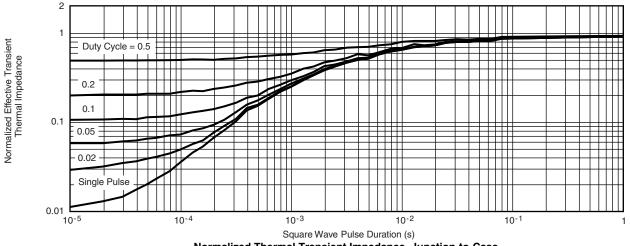




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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg271328.



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